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## Embedded OEM

### DRAM

- DDR3
- DDR2**
- DDR
- SDR
- Speciality

Flash

SSD

ADD2

Modems

[Home](#) > [Embedded OEM](#) > [DRAM](#) > [DDR2](#)

# DRAM DDR2

## SODIMM

RDIMM	UDIMM	SODIMM	mini DIMM
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DDR2 has been the standard memory solutions for applications in virtually all market segments from Servers, PCs and Notebooks to Printers, Networking and Storage systems and many more for several years providing superior cost and performance criteria. DDR2 has started to relinquish its role as the memory industry's mainstream technology to DDR3 and is forecasted to become a legacy product by early 2011

Available in power supply voltages of 1.8V (and 1.55V for FBDIMMs) and with transfer data rates from 400Mb/s to 800Mb/s and beyond, DDR2 has been designed in a wide range of applications providing designers with numerous module options to choose from. Wintec offers a wide range of DDR2 Module solutions. Please click on the link to find out more about our solutions.

### DDR2 - 200-Pin SODIMM - Registered ECC

Standard Profile (1.181") with Nominal Voltage (1.8V)

Density	Part Number	Rank	DIMM Config	Component Config	Voltage
1GB	WD2AE01GX809-xxxx-yyz	1 rank	128x72	128Mx8	1.8V
2GB	WD2AE02GX809-xxxx-yyz	1 rank	256x72	256Mx8	1.8V
4GB	WD2AE04GD809-xxxx-yyz	2 rank	512x72	512Mx8	1.8V

### DDR2 - 200-Pin SODIMM - Unbuffered ECC

Standard Profile (1.181") with Nominal Voltage (1.8V)

Density	Part Number	Rank	DIMM Config	Component Config	Voltage
1GB	WD2SE01GX809-xxxx-yy	1 rank	128x72	128Mx8	1.8V

<b>2GB</b>	WD2SE02GX818-xxxx-yy	2 rank	256x72	128Mx8	1.8V
	WD2SE02GX809-xxxx-yy	1 rank	256x72	256Mx8	1.8V
<b>4GB</b>	WD2SE04GX818-xxxx-yy	2 Rank	512x72	256Mx8	1.8V

## DDR2 - 200-Pin SODIMM - Unbuffered Non-ECC

Standard Profile (1.181") with Nominal Voltage (1.8V)

Density	Part Number	Rank	DIMM Config	Component Config	Voltage
<b>1GB</b>	WD2SN01GX808-xxxx-yy	1 rank	128x64	128Mx8	1.8V
<b>2GB</b>	WD2SN02GX816-xxxx-yy	2 rank	256x64	128Mx8	1.8V
	WD2SN02GX808-xxxx-yy	1 rank	256x64	256Mx8	1.8V
<b>4GB</b>	WD2SN04GX816-xxxx-yy	2 rank	512x64	256Mx8	1.8V
	WD2SN04GX808-xxxx-yy	1 rank	512x64	512Mx8	1.8V

(xxxxx) Modules Speed (MHz) and CAS Latency

= 800I: 800MHz CL6  
 800G : 800MHz CL5  
 667G : 667MHz CL5  
 533E : 533MHz CL4

DRAM Manufacturer and Die Revision

(yy) = P: Samsung                   A: A-Die  
 H: Micron                        B: B-Die  
 C: Hynix                         C: C-Die

Buffer / Register set (Only applies to Registered/Buffered modules)

(z) = I: Inphi  
 D: IDT  
 L: Intel